TFE4188 - Introduction to Lecture 2 ICs and ESD

Goal

Understand the real-world constraints on our IC

Understand why you must always handle ESD on an IC

Carsten Wulff 2023

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The project for 2023 is to design an integrated temperature sensor. The hope is that some will tapeout on the Google/Efabless Open MPW shuttle

The real world constrains our IC

Q: What blocks must our IC include?

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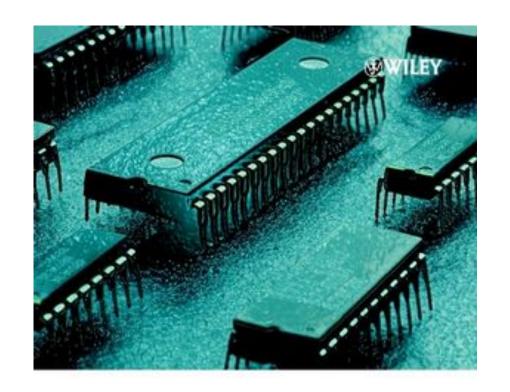
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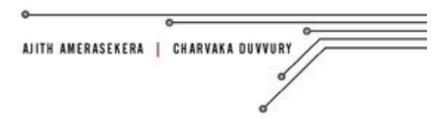
Electrostatic Discharge

If you make an IC, you must consider Electrostatic Discharge (ESD) Protection circuits

Standards for testing at JEDEC







When do ESD events occur?

Before/during PCB

After PCB

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Human body model (HBM)

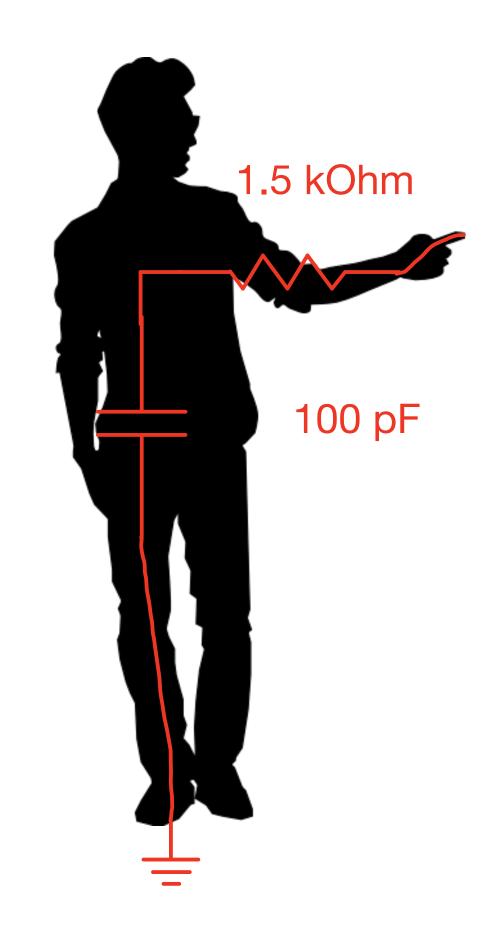
Human body model (HBM)

Charged device model (CDM)

System level ESD

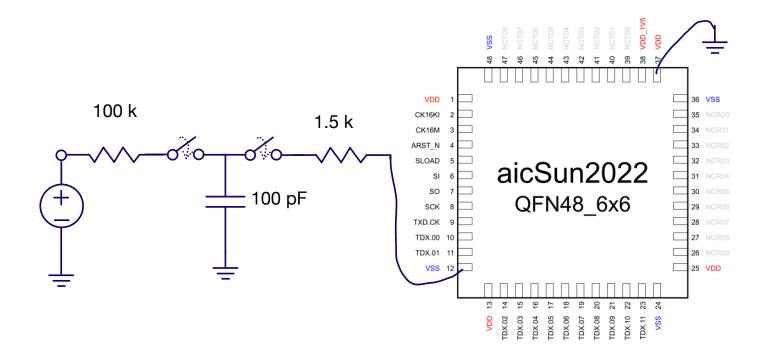
Human body model (HBM)

- Models a person touching a device with a finger
- Long duration (around 100 ns)
- Acts like a current source into a pin
- Can usually be handled in the I/O ring
- 4 kV HBM ESD is 2.67 A peak current

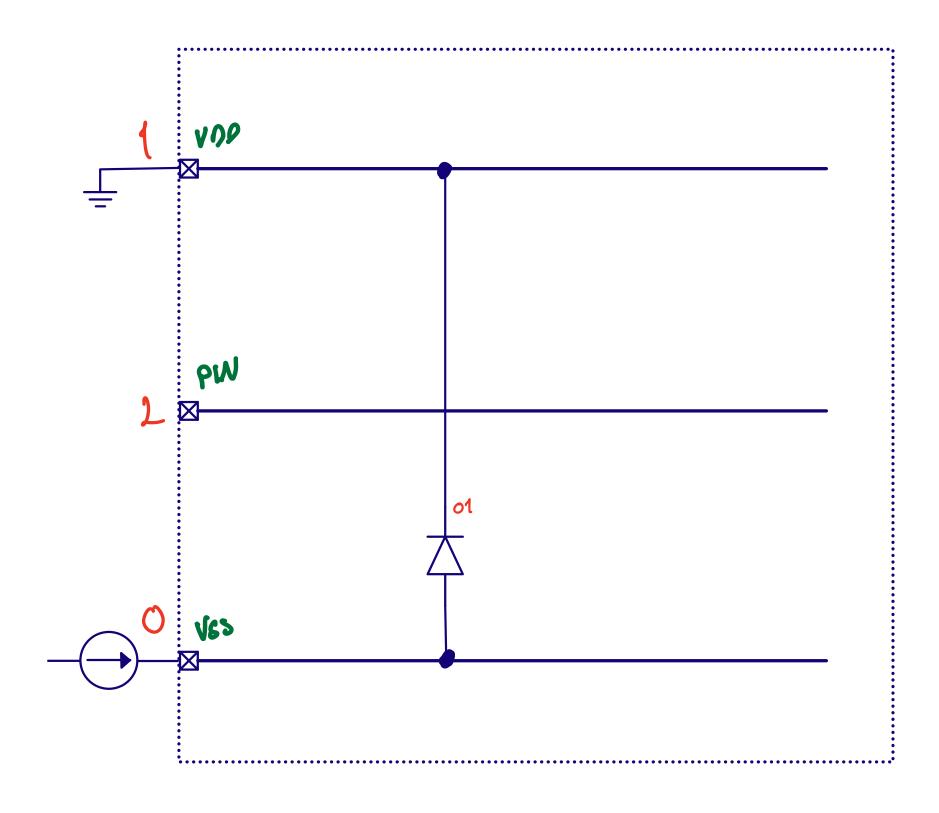


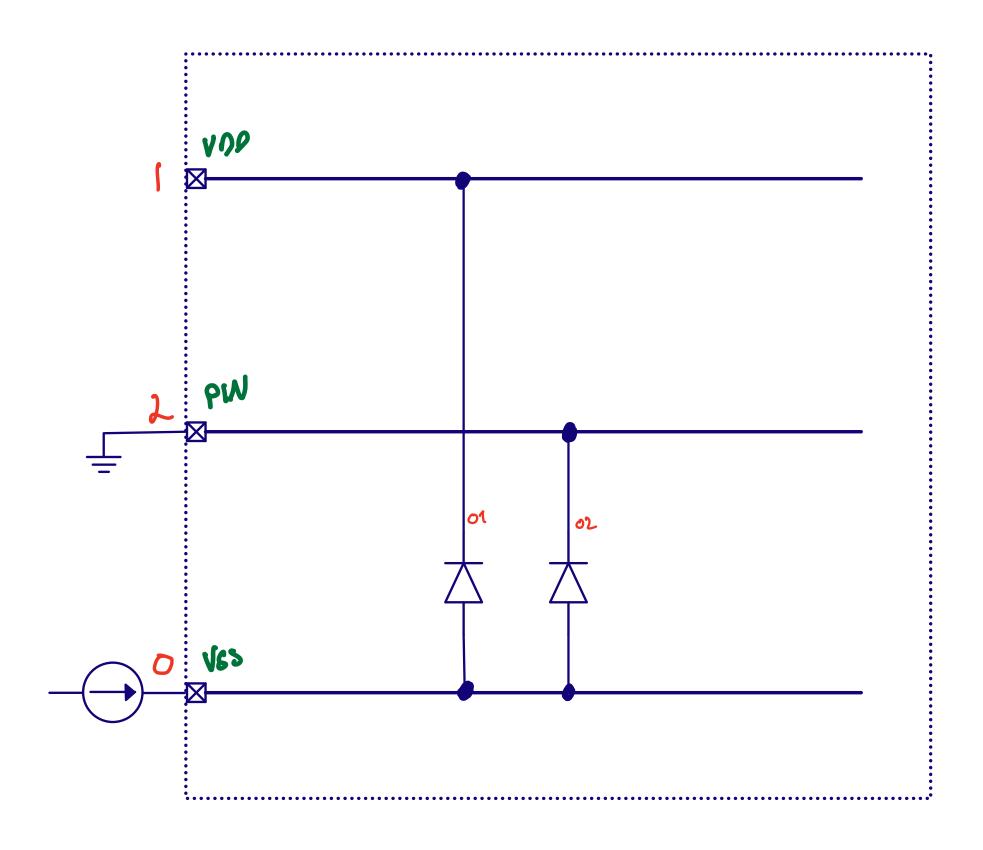
An ESD zap example

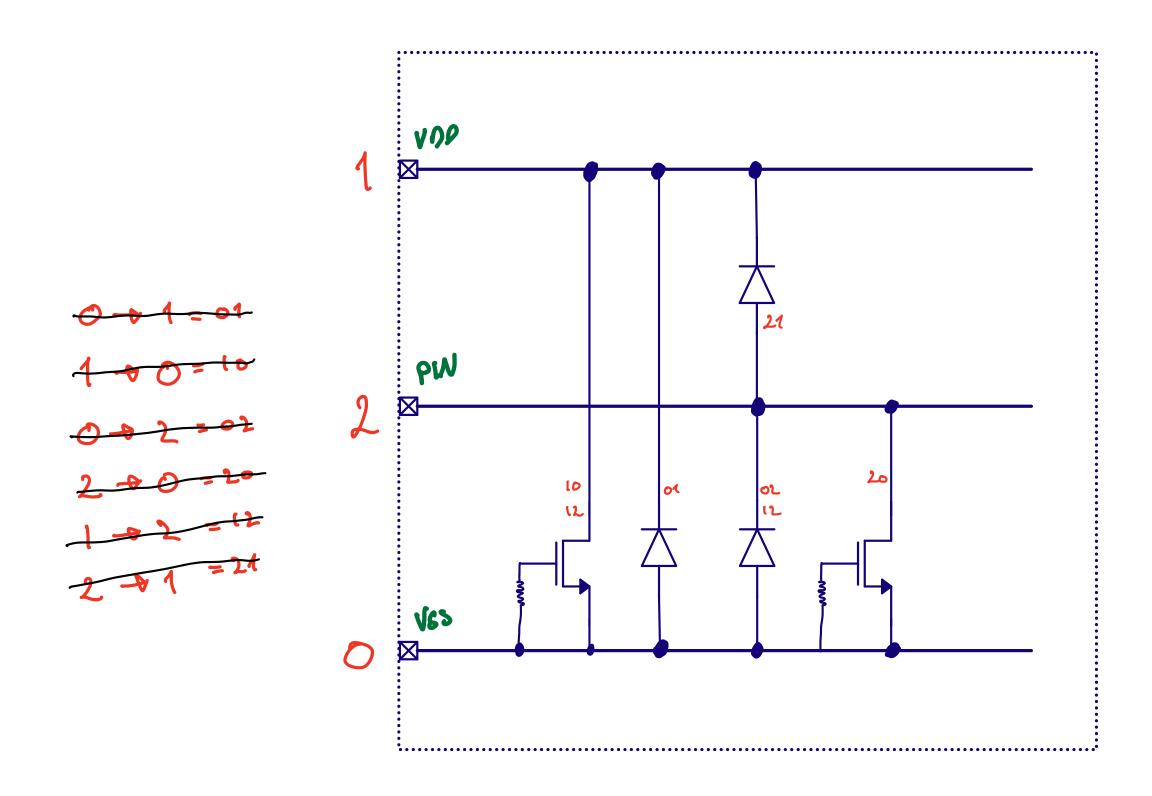
Imagine a ESD zap between VSS and VDD. How can we protect the device?

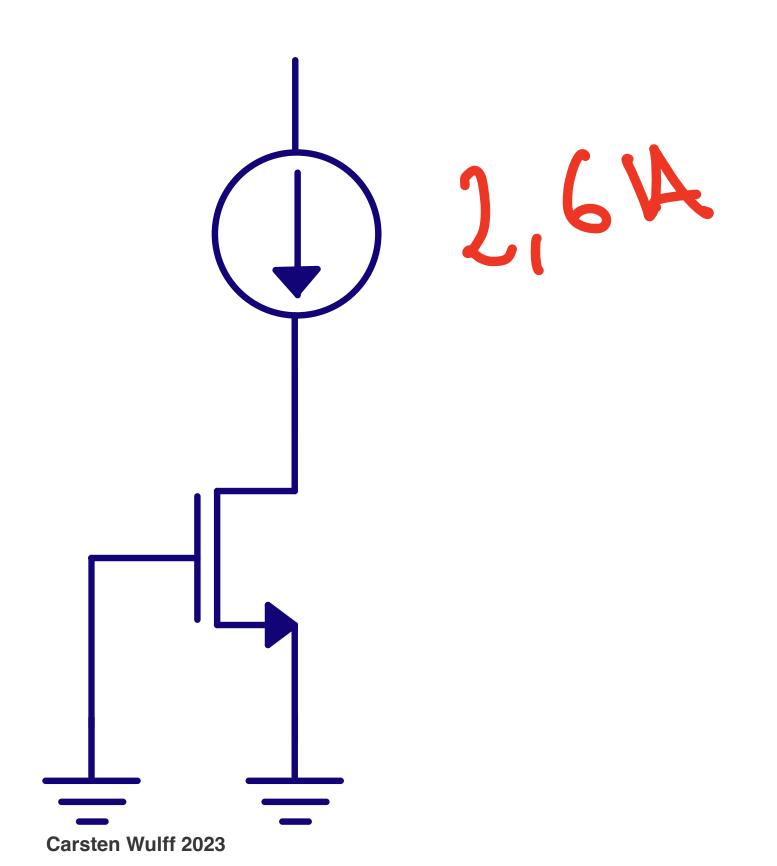


Permutations 1 * 0 * VØD * VØS 0 * 2 * VØS 2 * 0 PN * VØS 2 * 0 PN * VØS









Q: Why does this work?

If you don't do the layout right³

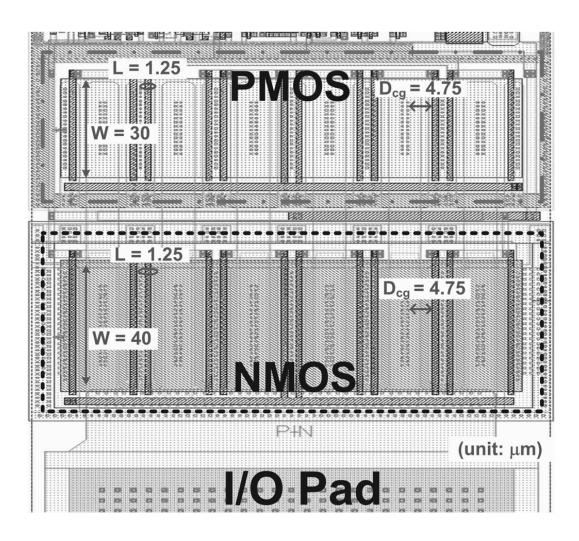


Fig. 5. Layout top view of the self-protecting fully silicided I/O buffer in a CMOS IC product.

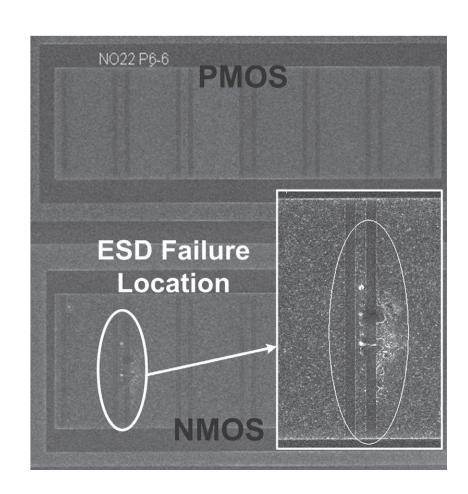
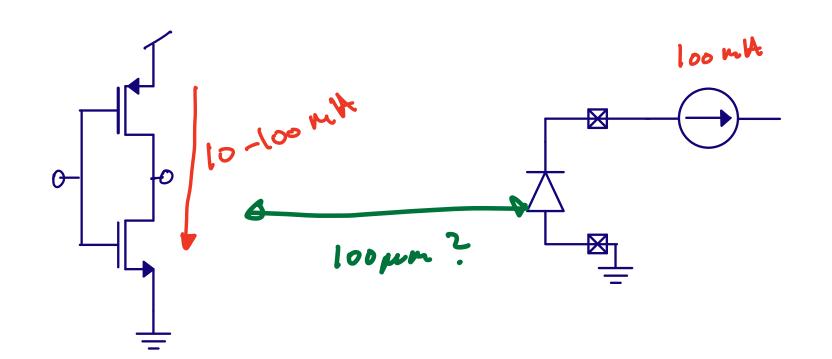


Fig. 6. SEM image of the fully silicided I/O buffer without ballasting after 2-kV PS-mode ESD stress. ESD failure is found on only one finger of the driver NMOS. Current filamentation is also observed on the surface of the driver NMOS without ballasting.

³New Ballasting Layout Schemes to Improve ESD Robustness of I/O Buffers in Fully Silicided CMOS Process



Q: How can current in one place lead to a current somewhere else?

You must always handle ESD on an IC

- Do everything yourself
- Use libraries from foundry
- Get help www.sofics.com

Thanks!